

Amendments to the Claims:

Claim 1 has been currently amended by merging claim 8 (previously dependent on claim 1) with it. No new matter is introduced.

Claim 14 has been added, dependent on claim 1. No new matter is introduced.

5 Listing of Claims:

1. (currently amended) A method for forming a light emitting diode comprising following steps:
forming a first stack;
forming a second reaction layer over said first stack;
10 forming a second stack;
forming a first reaction layer over said second stack;
holding together said first reaction layer and said second reaction layer by means of a transparent adhesive layer;
15 wherein the first and second reaction layers each comprise material selected from a group consisting of SiNx, Ti, and Cr.
2. (original) The method of claim 1 wherein the step of forming a first stack comprises following steps:
providing a first substrate;
20 forming a second contact layer on the first substrate;
forming a second cladding layer on the second contact layer;
forming an emitting layer on the second cladding layer;
forming a first cladding layer on the emitting layer;
forming a first contact layer on the first cladding layer; and
25 forming a transparent conductive layer on the first contact layer.

3. (original) The method of claim 2 further comprising following steps:

removing the first substrate;
 etching the second contact layer, the second cladding layer, the emitting layer, first
 cladding layer, and the first contact layer; and
 forming a first electrode on the second contact layer, and a second electrode on the
 transparent conductive layer.

4. (original) The method of claim 2 wherein the first substrate comprises at least one material selected from a group consisting of GaP, GaAs, and Ge.
5. (original) The method of claim 2 wherein the first contact layer and the second contact layer each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, and AlGaAs.
6. (original) The method of claim 2 wherein the first cladding layer, the emitting layer, and the second cladding layer each comprise AlGaInP.
7. (original) The method of claim 2 wherein the transparent conductive layer comprises at least one material selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, and Ni/Au.
8. (cancelled)
9. (original) The method of claim 1 wherein the transparent adhesive layer comprises at least one material selected from a group consisting of PI, BCB, and PFCB.
10. (original) The method of claim 1 wherein forming a second stack comprises forming a second substrate.

11. (original) The method of claim 10 wherein the second substrate comprises at least one material selected from a group consisting of SiC, Al₂O₃, glass materials, quartz, GaP, GaAsP, and AlGaAs.

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12. (original) The method of claim 1 wherein said first reaction layer and said second reaction layer are held together with the transparent adhesive layer by chemical bonds.

- 10 13. (original) The method of claim 12 wherein the chemical bonds are hydrogen bonds or ionic bonds.

14. (new) The method of claim 1 where the first and second reaction layers comprise SiNx.

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